# Power MOSFET -60V, 100mΩ, -4A, P-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

## Features

- 4V drive
- High ESD protection
- Low On-Resistance
- Pb-Free, Halogen Free and RoHS compliance

## **Typical Applications**

- Reverse Battery Protection
- High Side Load Switch

## SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

	<b>100 0 01</b>	/	
Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	-60	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC) (Note 2)	סו	-4	А
Drain Current (DC) (Note 3)	טי	-3	А
Drain Current (Pulse) PW $\leq 10\mu$ s, duty cycle $\leq 1\%$	, I IDD		А
Power Dissipation Ta=25°C(Note 2)	PD	1.9	W
Power Dissipation Ta=25°C(Note 3)	ΓD	0.9	W
Junction Temperature and Storage Temperature	Tj, Tstg	-55 to +175	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE RATINGS

Parameter		Symbol	Value	Unit	
Junction to Ambient	(Note 2)	Pola	78.1	°C/W	
	(Note 3)	R <sub>θ</sub> JA	160	°C/W	

Note 2 : Surface mounted on ceramic substrate( $1500mm^2 \times 0.8mm$ ).

Note 3 : Surface mounted on FR4 board using a  $92mm^2$ , 1 oz. Cu pad.

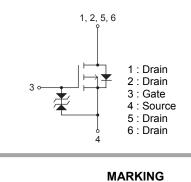


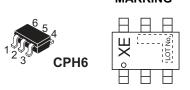
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VDSS	R <sub>DS</sub> (on) Max	ID Max
-60V	100mΩ@ –10V	
	135mΩ@ –4.5V	-4A
	145mΩ@ –4.0V	

#### ELECTRICAL CONNECTION P-Channel





# ORDERING INFORMATION

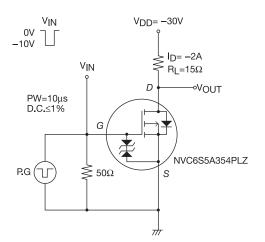
See detailed ordering and shipping information on page 6 of this data sheet.

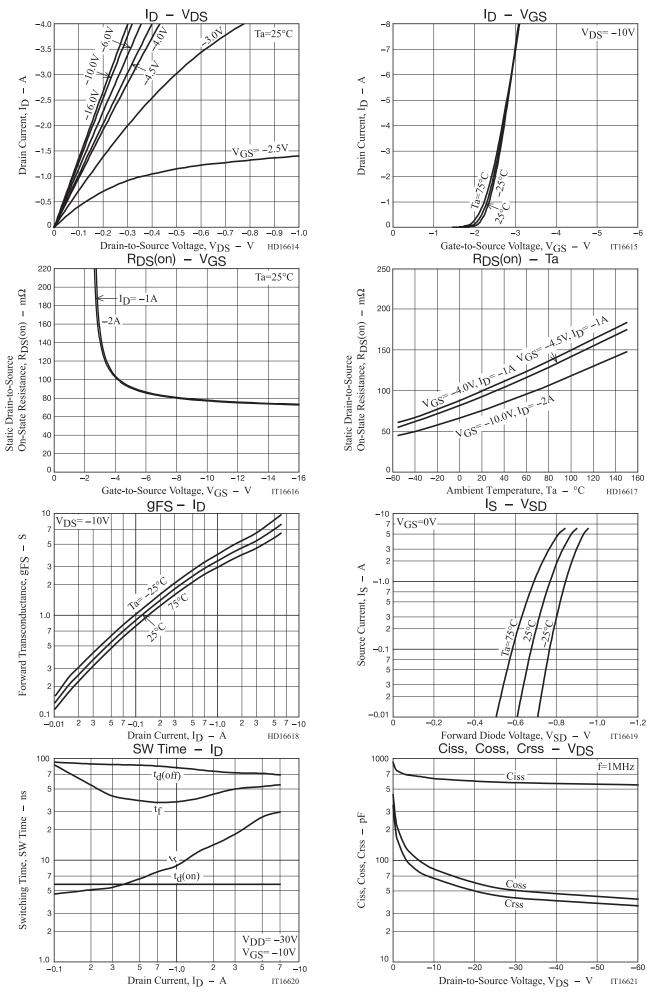
# **ELECTRICAL CHARACTERISTICS** at $Ta = 25^{\circ}C$ (Note 4)

Devenueter	Symbol			Value		
Parameter		Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-60			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V			-1	μA
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μA
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V
Forward Transconductance	9FS	V <sub>DS</sub> =-10V, I <sub>D</sub> =-2A		4.8		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)	I <sub>D</sub> =-2A, V <sub>GS</sub> =-10V		77	100	mΩ
		ID=-1A, VGS=-4.5V		96	135	mΩ
		ID=-1A, VGS=-4V		103	145	mΩ
Input Capacitance	Ciss			600		pF
Output Capacitance	Coss	V <sub>DS</sub> =–20V, f=1MHz		60		pF
Reverse Transfer Capacitance	Crss			50		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			5.8		ns
Rise Time	tr			12		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See Fig.1		78		ns
Fall Time	tf			40		ns
Total Gate Charge	Qg			14		nC
Gate to Source Charge	Qgs	V <sub>DS</sub> =-30V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-4A		1.6		nC
Gate to Drain "Miller" Charge	Qgd			3.4		nC
Forward Diode Voltage	VSD	IS=-4A, VGS=0V		-0.84	-1.2	V

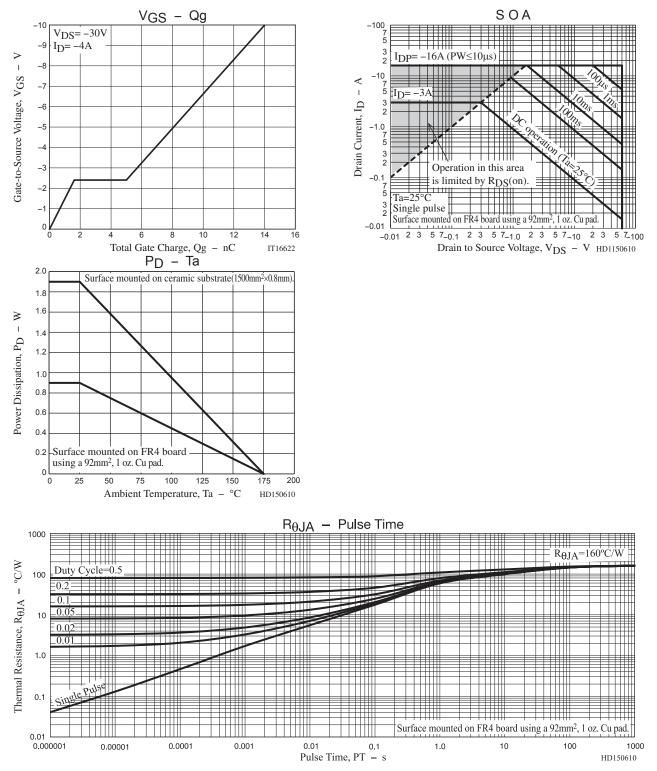
Note 4 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## Fig.1 Switching Time Test Circuit





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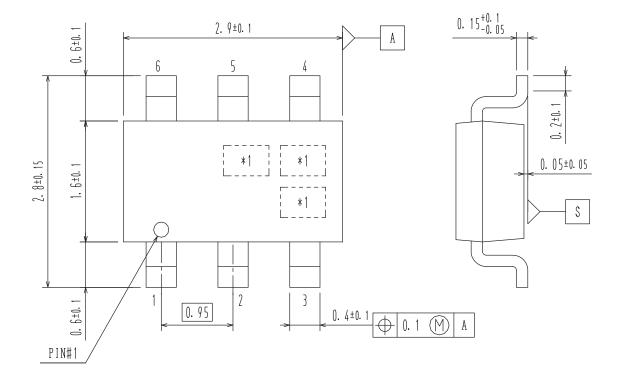


# PACKAGE DIMENSIONS

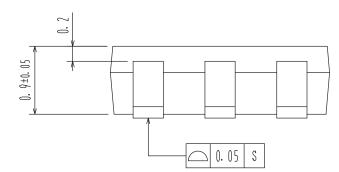
unit : mm

### CPH6

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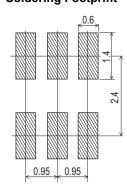


\*1:Lot indication



- 1 : Drain
- 2 : Drain
- 3 : Gate
- 4 : Source
- 5 : Drain
- 6 : Drain

Recommended Soldering Footprint



#### ORDERING INFORMATION

ORDERING INI ORMATION					
Device	Marking	Package	Shipping (Qty / Packing)		
NVC6S5A354PLZT1G	XE	CPH6 (Pb-Free / Halogen Free)	3,000 / Tape & Reel		

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

Note on usage : Since the NVC6S5A354PLZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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